**Product data sheet** 

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a SOT323 (SC-70) small Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Low R<sub>DSon</sub>
- Very fast switching
- Trench MOSFET technology

### 3. Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
$V_{GS}$	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> 25 °C	[1]	-	-	-1	Α
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; $I_D$ = -1 A; $T_j$ = 25 °C		-	175	200	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



20 V, 1 A P-channel Trench MOSFET

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D I
2	S	source		
3	D	drain	1 2	G
			SC-70 (SOT323)	017aaa094

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMF170XP	SC-70	plastic surface-mounted package; 3 leads	SOT323			

## 7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMF170XP	XD%

<sup>[1] % =</sup> placeholder for manufacturing site code

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
$V_{GS}$	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> 25 °C	[1]	-	-1	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-0.7	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-4	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	290	mW
			[1]	-	360	mW
		$T_{sp} = 25  ^{\circ}C$		-	1670	mW
Tj	junction temperature			-55	150	°C

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Symbol	Parameter	Conditions		Min	Max	Unit	
T <sub>amb</sub>	ambient temperature			-55	150	°C	
T <sub>stg</sub>	storage temperature			-65	150	°C	
Source-drain diode							
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-0.4	Α	

- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

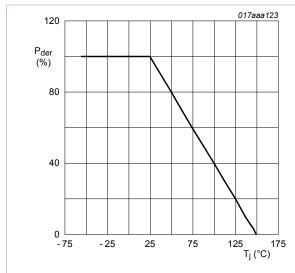


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

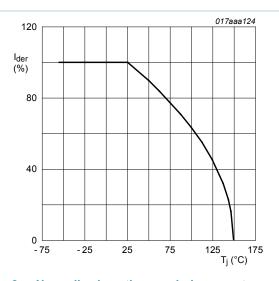
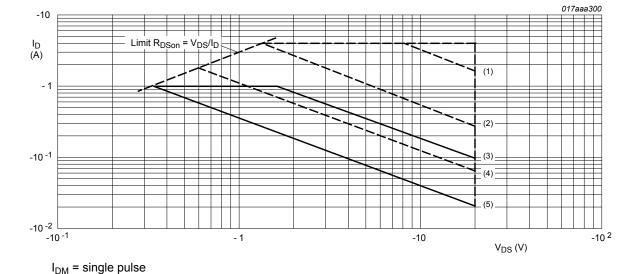


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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- (1)  $t_p = 1 \text{ ms}$
- (2)  $t_p = 10 \text{ ms}$
- (3) DC;  $T_{sp} = 25 \,^{\circ}\text{C}$
- (4)  $t_p = 100 \text{ ms}$
- (5) DC;  $T_{amb} = 25 \, ^{\circ}\text{C}$ ; drain mounting pad 6 cm<sup>2</sup>

Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

### Thermal characteristics

Table 6. **Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
fr	thermal resistance from junction to ambient	in free air	[1]	-	377	430	K/W
			[2]	-	305	350	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	65	75	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

PMF170XP

20 V, 1 A P-channel Trench MOSFET

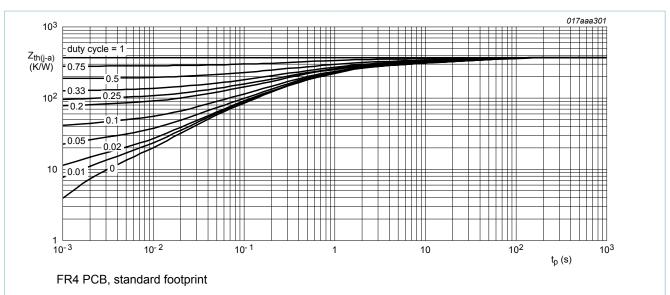


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

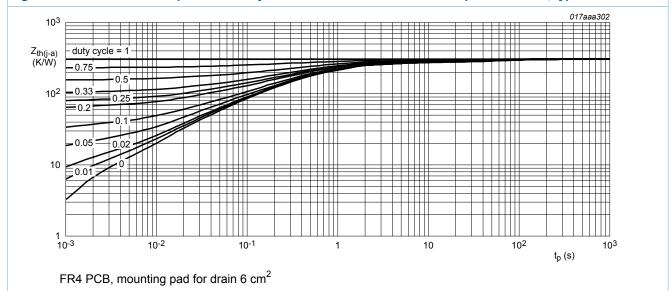


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

### 10. Characteristics

Table 7. Characteristics

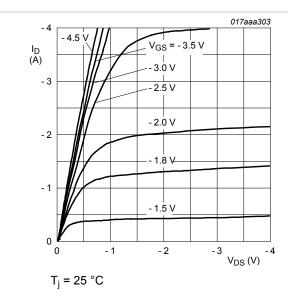
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static chara	Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$		-20	-	-	V	
V <sub>GSth</sub>	gate-source threshold voltage	$I_D$ = -250 A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C		-0.65	-0.9	-1.15	V	
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = -20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C		-	-	-1	μA	
		V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C		-	-	-10	μA	
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Product data sheet 29 October 2013 5 / 15

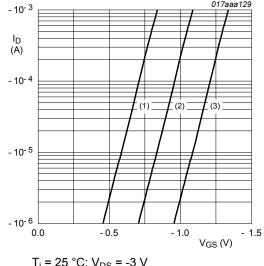
### 20 V, 1 A P-channel Trench MOSFET

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -12 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-100	nA
		V <sub>GS</sub> = 12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -1 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	175	200	mΩ
	resistance	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -1 A; T <sub>j</sub> = 150 °C	-	250	284	mΩ
		$V_{GS}$ = -2.5 V; $I_D$ = -1 A; $T_j$ = 25 °C	-	240	300	mΩ
g <sub>fs</sub>	forward transconductance	$V_{DS} = -5 \text{ V}; I_{D} = -1 \text{ A}; T_{j} = 25 \text{ °C}$	-	1.9	-	S
Dynamic cl	haracteristics		'			
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -10 V; $I_{D}$ = -1 A; $V_{GS}$ = -4.5 V; $T_{j}$ = 25 °C	-	2.6	3.9	nC
Q <sub>GS</sub>	gate-source charge		-	0.63	-	nC
$Q_{GD}$	gate-drain charge		-	0.53	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	280	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	43	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	30	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; $I_{D}$ = -1 A; $V_{GS}$ = -4.5 V;	-	10	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	16	-	ns
$t_{d(off)}$	turn-off delay time	]	-	31	-	ns
t <sub>f</sub>	fall time		-	13	-	ns
Source-dra	in diode		I		-	
$V_{SD}$	source-drain voltage	I <sub>S</sub> = -0.4 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	-0.7	-1.2	V

### 20 V, 1 A P-channel Trench MOSFET



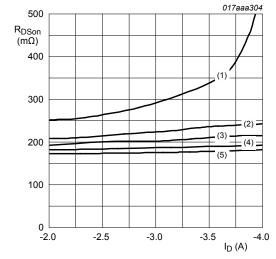
Output characteristics: drain current as a Fig. 6. function of drain-source voltage; typical values



$$T_i = 25 \,^{\circ}\text{C}; \, V_{DS} = -3 \,^{\circ}\text{V}$$

- (1) minimum values
- (2) typical values
- (3) maximum values

Sub-threshold drain current as a function of Fig. 7. gate-source voltage



$$(1) V_{GS} = -2.5 V$$

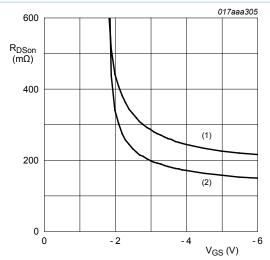
$$(2) V_{GS} = -3.0 V$$

$$(3) V_{GS} = -3.5 V$$

$$(4) V_{GS} = -4.0 V$$

$$(5) V_{GS} = -4.5 V$$

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

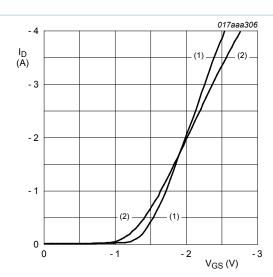


(1) 
$$T_i = 150 \, ^{\circ}C$$

(2) 
$$T_i = 25 \, ^{\circ}C$$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

### 20 V, 1 A P-channel Trench MOSFET

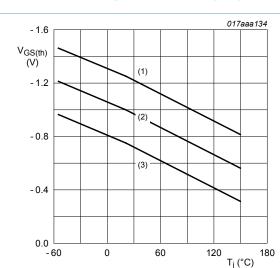


$$V_{DS} > I_{D} \times R_{DSon}$$

(1) 
$$T_j = 25 \, ^{\circ}C$$

(2) 
$$T_j = 150 \, ^{\circ}C$$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $I_D = -0.25 \text{ mA}; V_{DS} = V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature

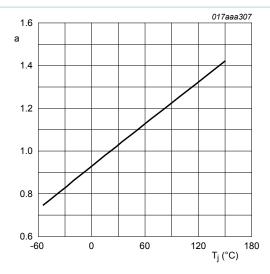
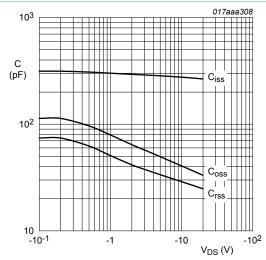


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



f = 1 MHz; V<sub>GS</sub> = 0 V

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

### 20 V, 1 A P-channel Trench MOSFET

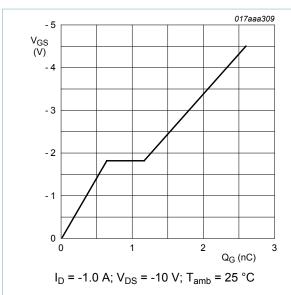


Fig. 14. Gate-source voltage as a function of gate charge; typical values

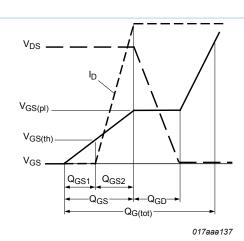
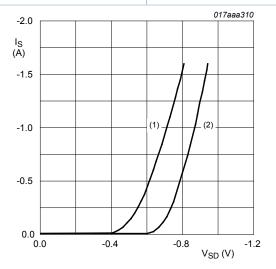


Fig. 15. Gate charge waveform definitions



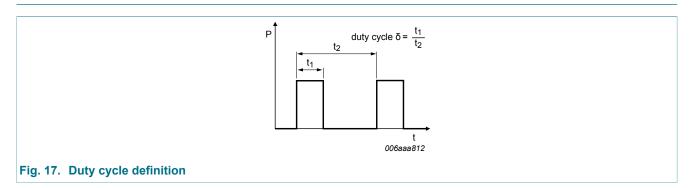
 $V_{GS} = 0 V$ (1)  $T_j = 150 \,^{\circ}C$ 

(2)  $T_i = 25 \,^{\circ}\text{C}$ 

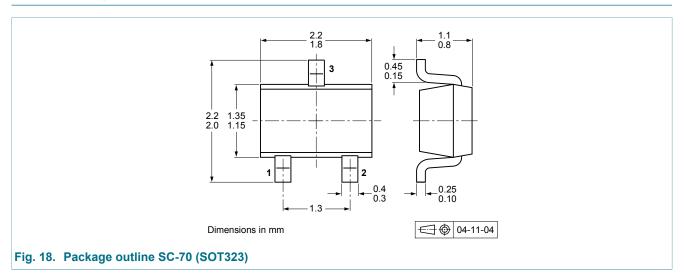
Fig. 16. Source current as a function of source-drain voltage; typical values

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### 11. Test information

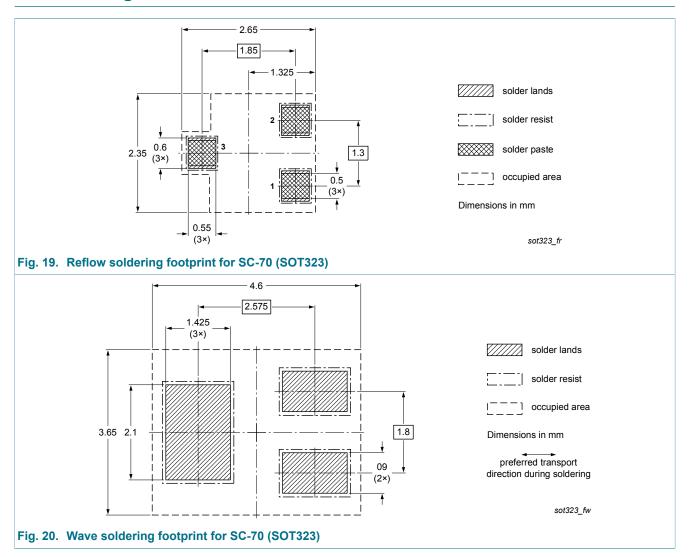


# 12. Package outline



### 20 V, 1 A P-channel Trench MOSFET

## 13. Soldering



20 V, 1 A P-channel Trench MOSFET

# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMF170XP v.2	20131029	Product data sheet	-	PMF170XP v.1
Modifications:	Figure 13 corrected			
PMF170XP v.1	20110902	Product data sheet	-	-

#### 20 V, 1 A P-channel Trench MOSFET

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#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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### 20 V, 1 A P-channel Trench MOSFET

### 16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	4
10	Characteristics	5
11	Test information	10
12	Package outline	10
13	Soldering	11
14	Revision history	12
15	Legal information	13
15.1	Data sheet status	13
15.2	Definitions	13
15.3	Disclaimers	13
15.4	Trademarks	14

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